MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGF1952A

Microwave Power MES FET (Leadless Ceramic Package)

DESCRIPTION

The MGF1952A is designed for use in S to Ku band power amplifiers.

The lead-less ceramic package assures minimum parasitic losses.

FEATURES

High gain and High P1dB

Glp=7.0dB, P1dB=17dBm (Typ.) @ f=12GHz

APPLICATION

S to Ku band power Amplifiers

QUALITY GRADE

GG

ORDERING INFORMATION

Tape & reel 3000pcs./reel

Outline Drawing

Fig.1

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

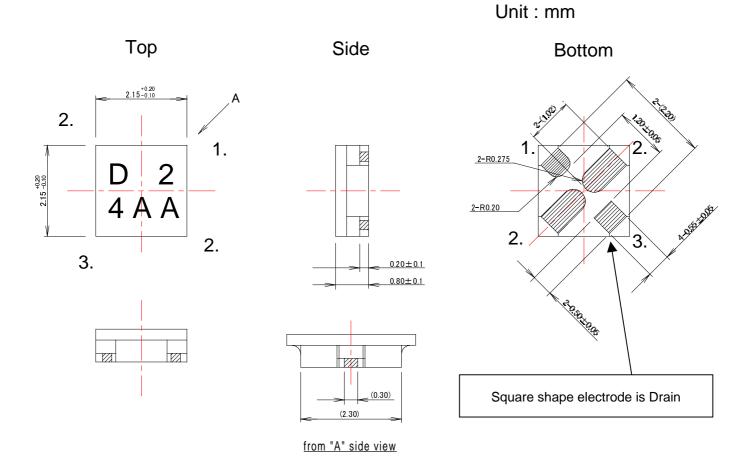
Symbol	Parameter	Ratings	Unit
V _{GDO}	Gate to drain voltage	-8	V
V_{GSO}	Gate to source voltage	-8	V
I _D	Drain current	240	mA
PT	Total power dissipation	600	mW
T _{ch}	Channel temperature	125	°C
T _{stg}	Storage temperature	-65 to +125	°C

Keep Safety first in your circuit designs! Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (I) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Synbol	Parameter	Test conditions	Limits		Unit	
			MIN.	TYP.	MAX	
V(BR)GDO	Gate to drain breakdown voltage	Ig=-60μA	-8	-15		V
IDSS	Saturated drain current	V _{GS} =0V,V _{DS} =3V	65	120	240	mA
V _{GS(off)}	Gate to source cut-off voltage	V _{DS} =3V,I _D =600μA	-0.3	-1.4	-3.5	V
P1dB	Output Power at 1dB gain	VDS=3V,ID=60mA	15	17		dBm
	Compression	f=12GHz				
Glp	Linear Power Gain	V _{DS} =3V,ID=60mA	5	7		dB
		f=12GHz,Pin=-5dBm				

Fig.1

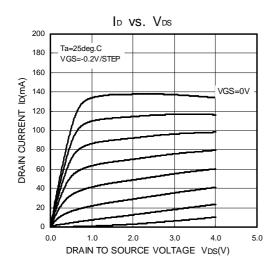


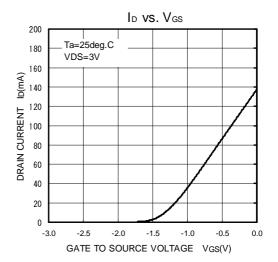
- 1. Gate
- 2. Source
- 3. Drain

MGF1952A

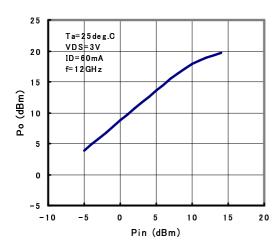
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TYPICAL CHARACTERISTICS (Ta=25°C)





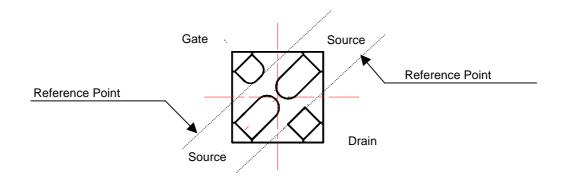




S PARAMETERS

(Conditions: VDS=3V,ID=60mA,Ta=25deg.C)

f	S11		S	21	S12		S12 S2		K	MAG/MSG
(GHz)	Mag.	Angle	Mag.	Angle	Mag.	Angle	Mag.	Angle		(dB)
1	0.963	-32.6	6.695	154.5	0.024	72.0	0.314	-24.7	0.21	24.4
2	0.888	-66.5	6.024	128.4	0.043	52.3	0.297	-51.3	0.38	21.4
3	0.822	-89.7	5.294	110.6	0.056	42.0	0.281	-66.0	0.51	19.7
4	0.764	-114.3	4.599	93.5	0.065	32.3	0.259	-83.0	0.64	18.5
5	0.720	-132.8	4.030	79.6	0.071	24.2	0.254	-94.1	0.77	17.5
6	0.685	-149.2	3.591	67.1	0.075	19.2	0.250	-100.0	0.90	16.8
7	0.660	-165.2	3.243	54.4	0.079	14.0	0.247	-104.2	1.01	15.5
8	0.643	-179.8	2.993	42.2	0.082	9.4	0.243	-108.3	1.10	13.7
9	0.629	165.3	2.785	30.5	0.088	4.4	0.232	-111.5	1.15	12.6
10	0.624	150.0	2.614	18.5	0.095	-0.8	0.214	-115.4	1.17	11.9
11	0.618	133.3	2.460	6.4	0.099	-8.3	0.179	-119.8	1.25	11.0
12	0.620	115.8	2.310	-6.9	0.104	-14.8	0.137	-125.6	1.29	10.2
13	0.639	98.6	2.163	-19.8	0.107	-21.6	0.085	-134.3	13.27	9.6
14	0.670	81.9	2.017	-33.9	0.111	-30.5	0.025	-176.9	1.32	9.2
15	0.709	66.3	1.846	-47.2	0.113	-39.4	0.063	61.7	1.33	8.7
16	0.765	52.1	1.700	-60.1	0.113	-48.6	0.145	47.0	1.25	8.8
17	0.815	37.9	1.537	-73.9	0.112	-57.5	0.237	37.8	1.18	8.8
18	0.850	25.1	1.353	-88.1	0.109	-67.0	0.328	29.2	1.16	8.5



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